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October 2013

## FDPF5N50NZU N-Channel UniFET<sup>TM</sup> II Ultra FRFET<sup>TM</sup> MOSFET 500 V, 3.9 A, 2.0 Ω

### Features

- $R_{DS(on)}$  = 1.7  $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 1.95 A
- Low Gate Charge (Typ. 9 nC)
- Low C<sub>rss</sub> (Typ. 4 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- ESD Improved Capability
- RoHS Compliant

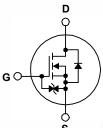
## Applications

- LCD/LED TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

## Description

UniFET<sup>TM</sup> II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. UniFET II Ultra FRFET<sup>™</sup> MOSFET has much superior body diode reverse recovery performance. Its t<sub>rr</sub> is less than 50nsec and the reverse dv/dt immunity is 20V/nsec while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore UniFET II Ultra FRFET MOSFET can remove additional component and improve system reliability in certain applications that require performance improvement of the MOSFET's body diode. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





## **MOSFET Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter		FDPF5N50NZU	Unit	
V <sub>DSS</sub>	Drain to Source Voltage			500	V	
V <sub>GSS</sub>	Gate to Source Voltage			±25	V	
ID	Drain Current	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)		3.9*		
	Drain Current	- Continuous (T <sub>C</sub> -	= 100 <sup>o</sup> C)	2.3*	A	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1) 15*		Α	
E <sub>AS</sub>	Single Pulsed Avalanche Energy		(Note 2)	135	mJ	
I <sub>AR</sub>	Avalanche Current		(Note 1)	3.9	Α	
E <sub>AR</sub>	Repetitive Avalanche Er	nergy	(Note 1)	7.8	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)			20	V/ns	
P <sub>D</sub>	Dewen Dissingtion	(T <sub>C</sub> = 25 <sup>o</sup> C)		30	W	
	Power Dissipation	- Derate above 25	°C	0.24	W/ºC	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
Τ <sub>L</sub>	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C	

Drain current limited by maximum junction temperature

## Thermal Characteristics

Symbol	Parameter	FDPF5N50NZU	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	4.1	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	°C/W

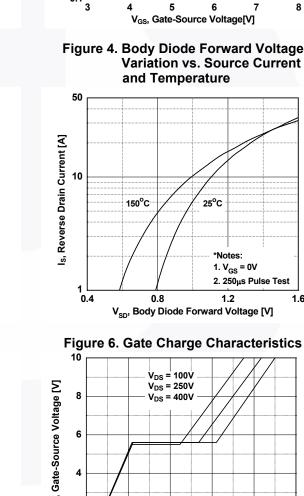
	Device Marking Device Pa		Package	e	Reel Size	Таре	e Width		Quantit	у
		TO-220	220F Tube I		N/A		50 units			
Electric	al Char	•acteristics ⊤ <sub>c</sub> =	25°C unless of	otherwise not	ed					
Symbol		Parameter		Te	st Conditions		Min.	Тур.	Max.	Unit
Off Chara	cteristic	:S							1	
BV <sub>DSS</sub>			oltage	lo = 250uA	$V_{00} = 0V T_0 =$	= 25°C	500	_	-	V
$\Delta BV_{DSS}$	Drain to Source Breakdown Voltage Breakdown Voltage Temperature Coefficient		-	$I_D = 250 \mu A, V_{GS} = 0V, T_C = 25^{\circ}C$		500		_		
$/\Delta T_{J}$				$I_D = 250 \mu A$ , Referenced to $25^{\circ}C$			-	0.5	-	V/°C
				V <sub>DS</sub> = 500V, V <sub>GS</sub> = 0V		-	-	25		
DSS	Zero G	Zero Gate Voltage Drain Current		$V_{DS} = 400V, V_{GS} = 0V, T_C = 125^{\circ}C$			-	-	250	μA
I <sub>GSS</sub>	Gate to	Gate to Body Leakage Current		$V_{GS}$ = ±25V,	$V_{DS} = 0V$		-	-	±10	μA
On Chara	cteristic	s								
V <sub>GS(th)</sub>	Gate T	hreshold Voltage		V <sub>GS</sub> = V <sub>DS</sub> ,	<sub>D</sub> = 250μA		3.0	-	5.0	V
R <sub>DS(on)</sub>	Static E	Drain to Source On Res	sistance	V <sub>GS</sub> = 10V, I			-	1.7	2.0	Ω
9 <sub>FS</sub>	Forwar	Forward Transconductance		$V_{DS} = 20V, I_D = 1.95A$			-	4.2	-	S
Dynamic	Charact	eristics								
C <sub>iss</sub>	Input C	apacitance		V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1MHz		-	365	485	pF	
C <sub>oss</sub>	Output	Capacitance				-	50	65	pF	
C <sub>rss</sub>	Revers	e Transfer Capacitance	e			-	4	8	pF	
Q <sub>g(tot)</sub>	Total G	ate Charge at 10V		$V_{DS} = 400V I_D = 3.9A$ $V_{GS} = 10V$ (Note 4)		-	9	12	nC	
Q <sub>gs</sub>	Gate to	Source Gate Charge				-	2	-	nC	
Q <sub>gd</sub>	Gate to	Drain "Miller" Charge				-	4	-	nC	
Switching	n Charac	teristics				. ,	I		1	
t <sub>d(on)</sub>	-	n Delay Time					-	12	35	ns
-a(on) t.		n Rise Time		$V_{DD}$ = 250V, I <sub>D</sub> = 3.9A $V_{GS}$ = 10V, R <sub>GEN</sub> = 25 $\Omega$ (Note 4)		-	-	19	50	ns
t <sub>d(off)</sub>		ff Delay Time				-	31	70	ns	
-a(011) t <sub>f</sub>		ff Fall Time				-	22	55	ns	
		de Characteristic	e			( )				
			-	Forward Cu	rent		- I		3.9	Α
		Maximum Continuous Drain to Source Did					_	_	15	A
s	Maximi	Maximum Pulsed Drain to Source Diode F						_	1.6	V
I <sub>S</sub> I <sub>SM</sub>		Source Diode Forward	d Voltage	$V_{GS} = 0V, I_{SD} = 3.9A$ $V_{GS} = 0V, I_{SD} = 3.9A$		-		1.0	. V	
I <sub>S</sub> I <sub>SM</sub> V <sub>SD</sub> t <sub>rr</sub>	Drain to	Source Diode Forward e Recovery Time	d Voltage				_	45	-	ns

3. I\_{SD}  $\leq$  3.9A, di/dt  $\leq$  200A/µs, V\_{DD}  $\leq$  BV\_{DSS}, Starting T\_J = 25^{\circ}C

4. Essentially Independent of Operating Temperature Typical Characteristics



#### **Typical Characteristics Figure 1. On-Region Characteristics** Figure 2. Transfer Characteristics 10 10 V<sub>GS</sub> = 15.0 V 10.0 V 8.0 V 7.0 V 6.5 V Drain Current[A] I<sub>D</sub>, Drain Current[A] 6.0 V 1 5.5 V 150°C 5.0 V ق 0.1 Notes 1. 250µs Pulse Test 2. T<sub>C</sub> = 25<sup>o</sup>C 0.1 0.03 25 3 4 10 0.1 1 V<sub>DS</sub>, Drain-Source Voltage[V] Figure 3. On-Resistance Variation vs. **Drain Current and Gate Voltage** 3.6 50 Drain-Source On-Resistance 9.1 9.1 9.1 Reverse Drain Current [A] R<sub>DS(ON)</sub> [Ω], 10 V<sub>GS</sub> = 10V V<sub>GS</sub> = 20V <u></u>。 \*Note: T<sub>c</sub> = 25°C 1.2 1 0 2 4 6 8 10 0.4 I<sub>D</sub>, Drain Current [A] **Figure 5. Capacitance Characteristics** 10 800 Ciss = Cgs + Cgd (Cds = shorted) Coss = Cds + Cgd V<sub>GS</sub>, Gate-Source Voltage [V] Crss = Cgd 8 600 Capacitances [pF] 6 Ciss 400 \*Note: 4 Coss 1. V<sub>GS</sub> = 0V 2. f = 1MHz 200 2 Crss 0 0 0.1 1 10 30 0 <sup>2</sup>Q<sub>q</sub>, Total Gate Charge [nC]<sup>8</sup> V<sub>DS</sub>, Drain-Source Voltage [V]



-55°C

25°C

\*Notes:

1. V<sub>DS</sub> = 20V 2. 250µs Pulse Test

8

1.6



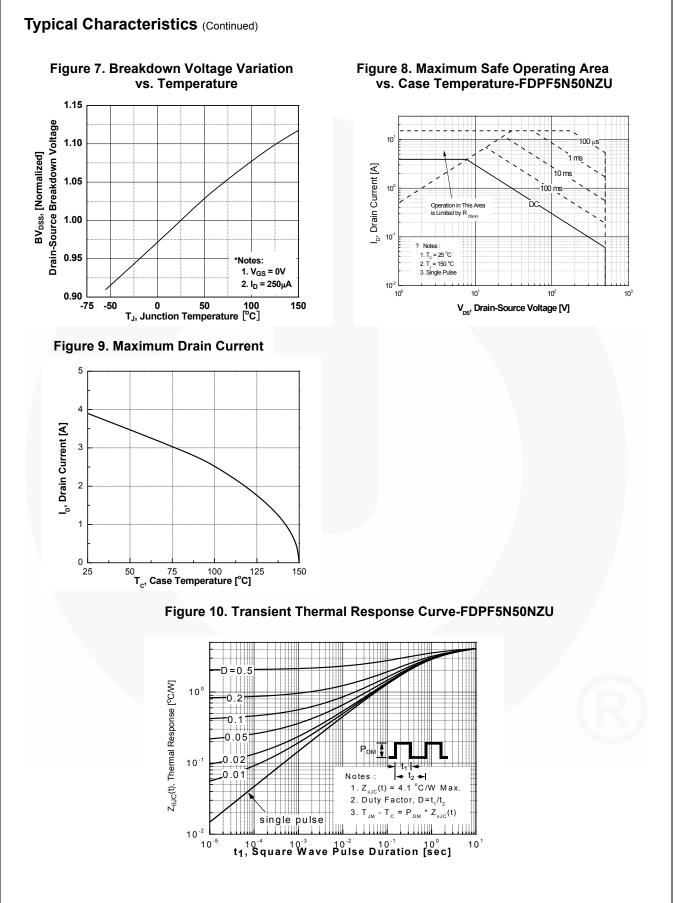
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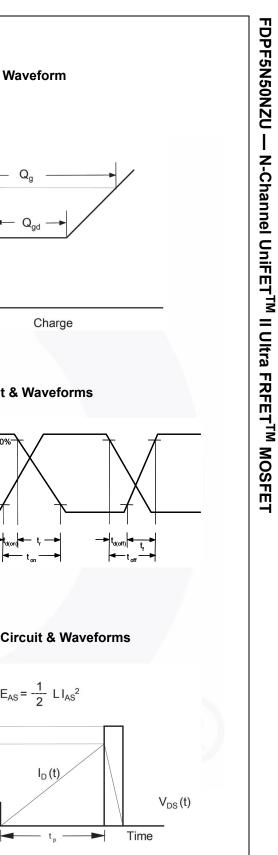
\*Note: I<sub>D</sub> = 3.9A

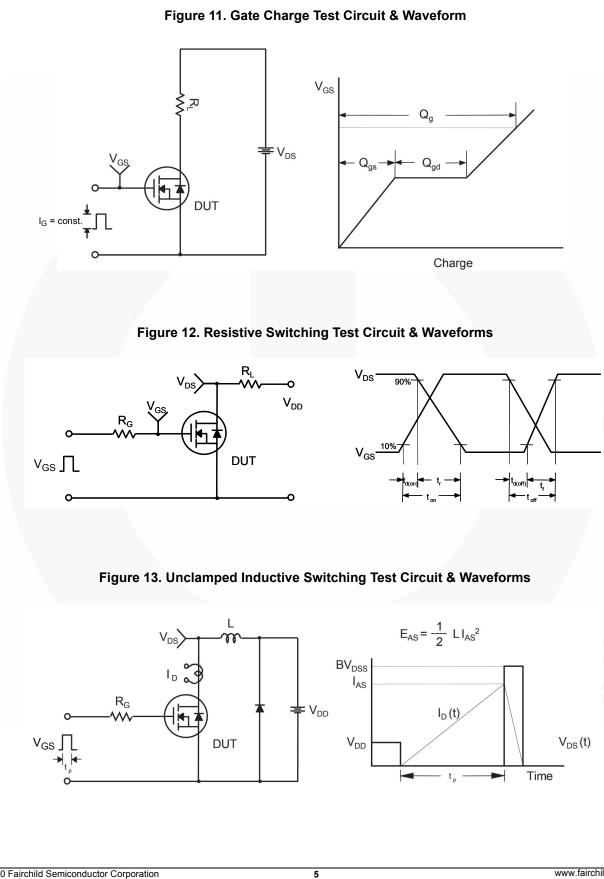
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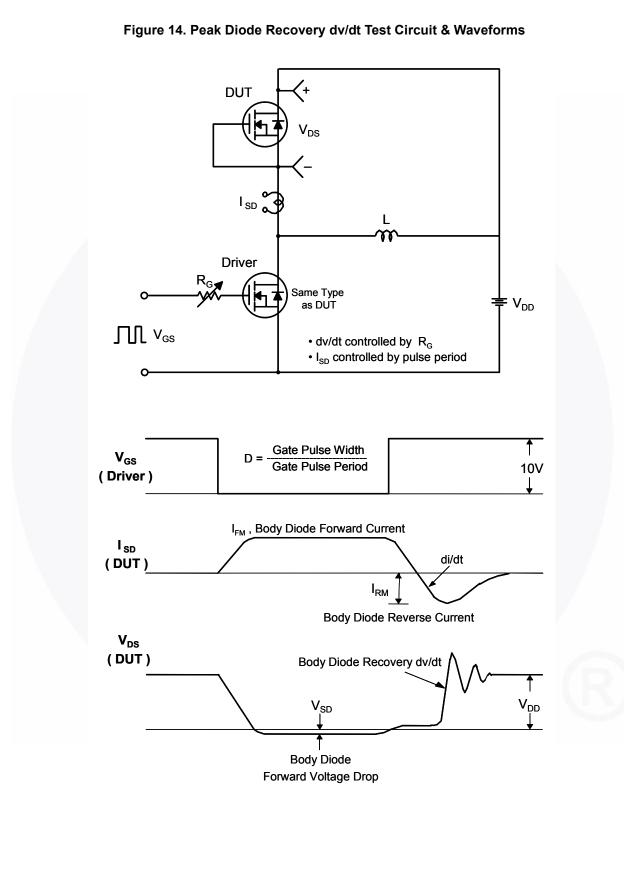
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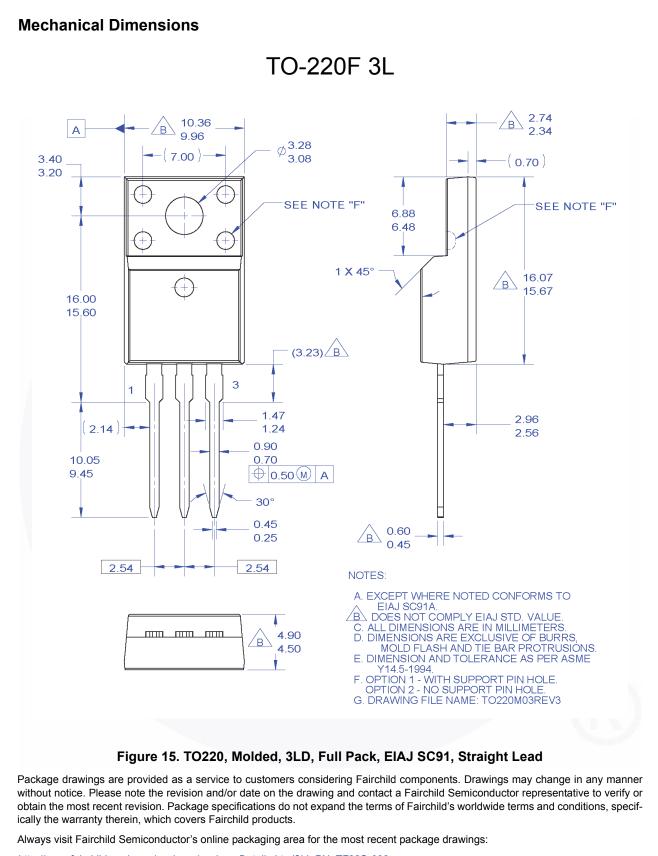


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**Dimension in Millimeters** 

FDPF5N50NZU — N-Channel UniFET<sup>TM</sup> II Ultra FRFET<sup>TM</sup> MOSFET



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